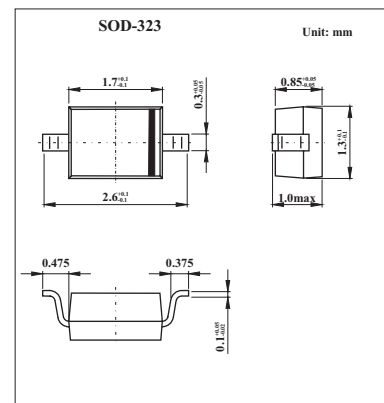


1PS76SB10

■ Features

- Low forward volatge
- Guard ring protected
- Very small plastic SMD package.



■ Absolute Maximum Ratings Ta = 25°C

PARAMATER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	V _R			30	V
continuous forward current	V _F			200	mA
repetitive peak forward current	T _{FRM}	tp ≤ 1 s; δ ≤ 0.5		300	mA
non-reetitiive peak forward current	T _{FSM}	tp < 10 ms		600	mA
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _j			125	°C
operating ambient temperature	T _{amb}		-65	+125	°C

■ Electrical Characteristics Ta = 25°C

PARAMATER	SYMBOL	CONDITIONS	MAX	UNIT
forward volatge	V _F	I _F = 0.1 mA	240	mV
		I _F = 1 mA	320	
		I _F = 10 mA	400	
		I _F = 30 mA	500	
		I _F = 100 mA	800	
reverse current	I _R	V _R = 25 V; note 1;	2	μA
diode capacitance	C _d	f = 1 MHz; V _R = 1V;	10	pF

Note

1. Pulsed test: tp = 300 μs; δ = 0.02.

■ Marking

Marking	S0
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